

## Abstract

A Si sputtering target that in the measurement of crystal face orientation of sputtering surface according to X-ray diffractometry, exhibits a ratio of peak intensity of (111) face ( $I_{(111)}$ ) to peak intensity of (220) face ( $I_{(220)}$ ) of Si, ( $I_{(111)}/I_{(220)}$ ), falling within the range of  $1.8 \pm 0.3$ . The Si sputtering target comprises, for example, an Si sintered material of 70 to 95 % relative density. With respect to sputtering films such as Si oxide film, the film thickness characteristics, film formation cost, etc. can be improved by the use of this Si sputtering target.